

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Canceled).

Claim 2 (Currently Amended): ~~Method~~ The method as recited in claim ~~1~~ 12, wherein an adhesive material is used for the attachment layer.

Claim 3 (Currently Amended): ~~Method~~ The method as recited in claim 2, wherein an adhesive material having a lower adhesion to the front face surface of the wafer at a higher temperature is used.

Claim 4 (Currently Amended): ~~Method~~ The method as recited in claim 2 wherein ~~the individual release of the semiconductor circuits are individually released from the carrier is performed mechanically~~ by overcoming the adhesion force of the attachment material layer to the front face surface of the wafer.

Claim 5 (Currently Amended): ~~Method~~ The method as recited in claim ~~±~~ 12, wherein the substrate is reduced in thickness to a thickness of less than 100  $\mu\text{m}$ .

Claim 6 (Currently Amended): ~~Method~~ The method as recited in claim ~~±~~ 12, wherein the separating trenches are produced by means of a photolithographic etching process.

Claims 7-8 (Canceled).

Claim 9 (Currently Amended)): ~~Method~~ The method as recited in claim ~~±~~ 12, wherein the ~~deposition of~~ back face metallization is ~~performed~~ deposited after production of the separating trenches.

Claim 10 (Currently Amended): ~~Method~~ The method as recited in claim 6, wherein a common photolithographic mask is used for the production of the passage holes and the separating trenches.

Claim 11 (Currently Amended). ~~Method~~ The method as recited in claim ~~±~~ 12, wherein an electrical function test of the semiconductor circuits is performed after separation.

Claim 12 (New): A method for producing individual monolithically integrated semiconductor circuit arrangements from a wafer composite substrate comprising the following steps:

- (a) forming a plurality of separate component structures comprising monolithic semiconductor circuits and conductive surfaces on a front face surface of a wafer;
- (b) covering the front face surface of the wafer with a protective layer to form a wafer composite substrate;
- (c) attaching the wafer to a support via an attachment layer applied over the support;
- (d) reducing the substrate to a selected thickness;
- (e) producing passage holes through the substrate up to the conductive surfaces on the front face surface;
- (f) producing separating trenches between the monolithic semiconductor circuits up to or into the attachment layer, including removal of the protective layer under the separating trenches and lateral under-etching of the substrate;

(g) depositing a back face metallization on a back face of the substrate and forming electrical connections through the passage holes; and

(h) individually releasing the semiconductor circuits from the support for further individual processing.